



# TECHNICAL UNIVERSITY OF MOMBASA

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SCHOOL OF ENGINEERING AND TECHNOLOGY

DEPARTMENT OF MEDICAL ENGINEERING

## UNIVERSITY EXAMINATION FOR:

BACHELOR OF SCIENCE IN MEDICAL ENGINEERING

ECL 4404: MEDICAL OPTICS II.

## END OF SEMESTER SUPPLEMENTARY EXAMINATION

**SERIES:** NOVEMBER, 2024

**TIME:** 2 HOURS

**DATE:** NOVEMBER, 2025

### Instructions to Candidates

You should have the following for this examination

*-Answer Booklet, examination pass and student ID*

This paper consists of FIVE questions. Answer question ONE and any other TWO

**Do not write on the question paper.**

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### Question ONE

- (a) Discuss the essential requirements for the construction of a laser. (10 marks)
- (b) A 3mW laser beam of wavelength  $\lambda = 6 \times 10^{-5}$  is focused by a convex lens. The focal length of the lens is 5 cm and radius of the circular aperture is 1 cm.
- (i) Find the intensity of the focused spot.
- (ii) If the coherence time of the laser is 50ns, find the monochromaticity of the source. (7 marks)
- (c) Describe qualitatively how a He-Ne laser works. (13 marks)

## Question TWO

- (a) Distinguish between temporal and spatial coherence. (3 marks)
- (b) Describe metastable states. Give examples (3 marks)
- (c) Calculate the gain constant  $\alpha_{12}$  of a laser beam from the following data  $N_2, N_1 = 5 \times 10^{16} \text{ cm}^{-3}$ ,  $\lambda_0 = 65000 \text{ \AA}$ , line-width  $\lambda = 15 \text{ \AA}$  and the lifetime for spontaneous emission  $= 2 \times 10^{-4} \text{ s}$  (7 marks)
- (d) Using an energy level diagram describe the principle of operation of Nd:YAG laser. (7 marks)

## Question THREE

- (a) Describe qualitatively of operation of carbon diode laser with the aid of energy band diagrams. (15 marks)
- (b) Calculate the ratio of stimulated to spontaneous emission rate at a temperature of 250 for sodium D lines. (5 marks)

## Question FOUR

- (a) Explain the concept of negative temperature in connection with the operation of a laser. (3 marks)
- (b) (i) By considering the rate equations for a three level laser, derive an expression for the threshold population inversion in terms of the laser parameters. Hence compare the pump power required to bring a three level and four level laser to threshold.
- (ii) Calculate the threshold pumping power for an Nd: glass laser, given that the critical population inversion is  $9 \times 10^{21} \text{ m}^{-3}$ , the spontaneous lifetime is  $300 \mu\text{s}$  and that the upper laser level is at an energy of 1.4 eV. (10 marks)
- (c) Discuss the application of lasers in medical field. (5 marks)
- (d) Explain high monochromaticity and high directionality of laser radiation. (2 marks)

## Question FIVE

- (a) Compare the ideal light output against current characteristics for the injection laser with one from a more typical device. Discuss the major points on the characteristics and indicate why the two differ. (5 marks)
- (b) For  $2p \rightarrow 1s$  transition in hydrogen atom, the mean spontaneous lifetime is  $1.66 \times 10^{-8} \text{ sec}$ . and the frequency of emitted radiation is  $2.4 \times 10^{15} \text{ Hz}$ . Calculate the probability of stimulated emission (3.5 marks)
- (c) With the help of energy level diagrams discuss the liquid dye lasers. (11.5 marks)

## PHYSICAL CONSTANTS

|                            |                                     |
|----------------------------|-------------------------------------|
| Permittivity of free space | $8.854 \times 10^{-12} \text{ F/M}$ |
| Permeability of free space | $4\pi \times 10^{-7} \text{ H/M}$   |
| Electron charge            | $1.602 \times 10^{-19} \text{ C}$   |
| Electron rest mass         | $9.108 \times 10^{-31} \text{ kg}$  |
| Electron charge/mass ratio | $1.759 \times 10^{11} \text{ C/kg}$ |
| Photon rest mass           | $1836m$                             |
| Planck's constant          | $6.625 \times 10^{-34} \text{ Js}$  |
| Boltzmann's constant       | $1.38 \times 10^{-23} \text{ J/K}$  |
| Speed of light             | $3 \times 10^8 \text{ ms}^{-1}$     |
| kT at room temperature     | $0.0259 \text{ eV}$                 |

## Properties of some common semiconductors at room temperature (300K)

|                                                  | Silicon              | Germanium            |
|--------------------------------------------------|----------------------|----------------------|
| Relative permittivity, $\epsilon_r$              | 11.8                 | 16                   |
| Energy gap, E eV                                 | 1.08                 | 0.66                 |
| Electron mobility, $\mu_e \text{ m}^2/\text{Vs}$ | 0.13                 | 0.38                 |
| Hole mobility, $\mu_h \text{ m}^2/\text{Vs}$     | 0.05                 | 0.18                 |
| Intrinsic concentration, $n_i \text{ m}^{-3}$    | $1.4 \times 10^{16}$ | $2.5 \times 10^{19}$ |
| Density of state at CB, $N_c \text{ m}^{-3}$     | $2.8 \times 10^{25}$ | $1 \times 10^{25}$   |
| Density of state at VB, $N_v \text{ m}^{-3}$     | $1 \times 10^{25}$   | $1.4 \times 10^{24}$ |
| Effective electron mass, $m_c^*$                 | 1.1m                 | 0.55m                |
| Effective hole mass, $m_{h*}$                    | 0.56m                | 0.37m                |